



AOP605

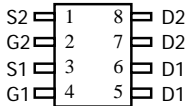
Complementary Enhancement Mode Field Effect Transistor

General Description

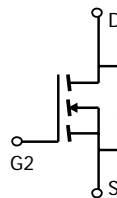
The AOP605 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs form a high-speed power inverter, suitable for a multitude of applications. *Standard Product AOP605 is Pb-free (meets ROHS & Sony 259 specifications). AOP605L is a Green Product ordering option. AOP605 and AOP605L are electrically identical.*

Features

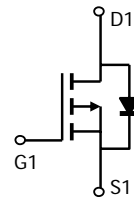
	n-channel	p-channel
V_{DS} (V)	30V	-30V
I_D = 7.5A (V_{GS} = 10V)		-6.6A (V_{GS} = -10V)
$R_{DS(ON)}$		
	< 28m Ω (V_{GS} = 10V)	< 35m Ω (V_{GS} = -10V)
	< 43m Ω (V_{GS} = 4.5V)	< 58m Ω (V_{GS} = -4.5V)



PDIP-8



n-channel



p-channel

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units	
Drain-Source Voltage	V_{DS}	30	-30	V	
Gate-Source Voltage	V_{GS}	± 20	± 20	V	
Continuous Drain Current ^A	I_D	$T_A=25^\circ\text{C}$	7.5	-6.6	A
		$T_A=70^\circ\text{C}$	6	-5.3	
Pulsed Drain Current ^B	I_{DM}	30	-30		
Power Dissipation	P_D	$T_A=25^\circ\text{C}$	2.5	2.5	W
		$T_A=70^\circ\text{C}$	1.6	1.6	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ\text{C}$	

Thermal Characteristics: n-channel

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	40	50	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	67	80
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	33	40	$^\circ\text{C/W}$

Thermal Characteristics: p-channel

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	38	50	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	66	80
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	30	40	$^\circ\text{C/W}$

n-channel MOSFET Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1	1.8	3	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	30			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =7.5A T _J =125°C		22.6	28	mΩ
		V _{GS} =4.5V, I _D =6.0A		33	43	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =7.5A	12	16		S
V _{SD}	Body Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.76	1	V
I _S	Maximum Body-Diode Continuous Current				4	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		680	820	pF
C _{oss}	Output Capacitance.			102		pF
C _{rss}	Reverse Transfer Capacitance			77		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		3	3.6	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =4.5V, V _{DS} =15V, I _D =7.5A		13.84	16.6	nC
Q _g	Total Gate Charge			6.74	8.1	nC
Q _{gs}	Gate Source Charge			1.82		nC
Q _{gd}	Gate Drain Charge			3.2		nC
t _{D(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =15V, R _L =2.0Ω, R _{GEN} =6Ω		4.6		ns
t _r	Turn-On Rise Time			4.1		ns
t _{D(off)}	Turn-Off Delay Time			20.6		ns
t _f	Turn-Off Fall Time			5.2		ns
t _{rr}	Body Diode Reverse Recovery time	I _F =7.5A, dI/dt=100A/μs		16.5	20	ns
Q _{rr}	Body Diode Reverse Recovery charge	I _F =7.5A, dI/dt=100A/μs		7.8		nC

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev 3 : June 2005

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: N-CANNEL

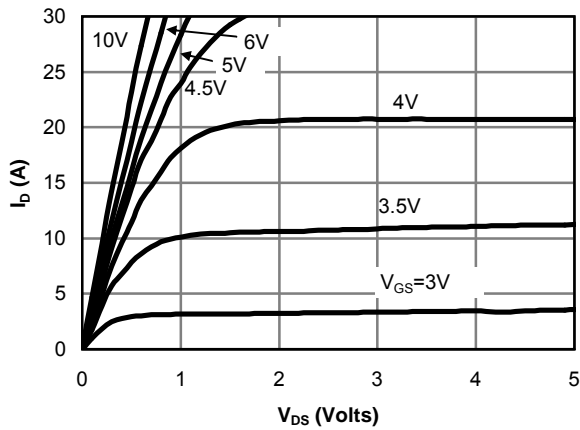


Fig 1: On-Region Characteristics

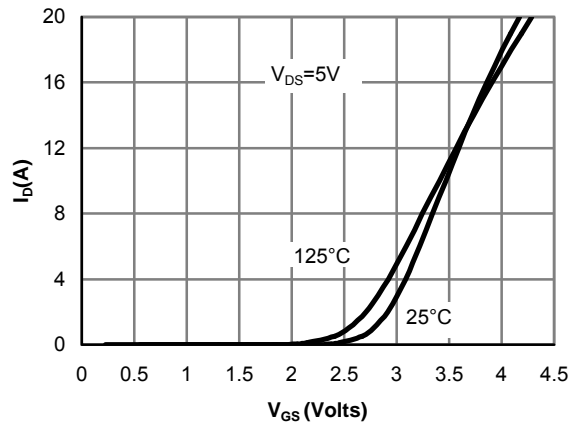


Figure 2: Transfer Characteristics

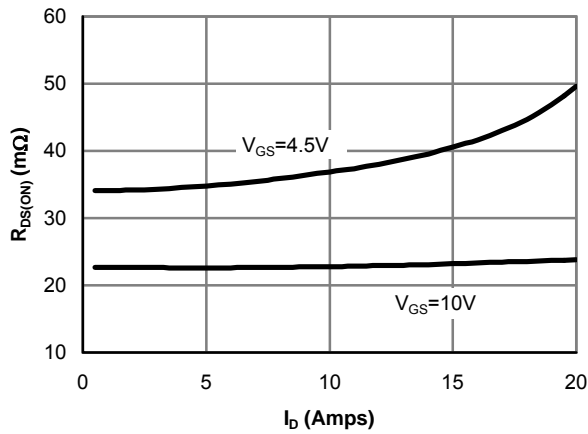


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

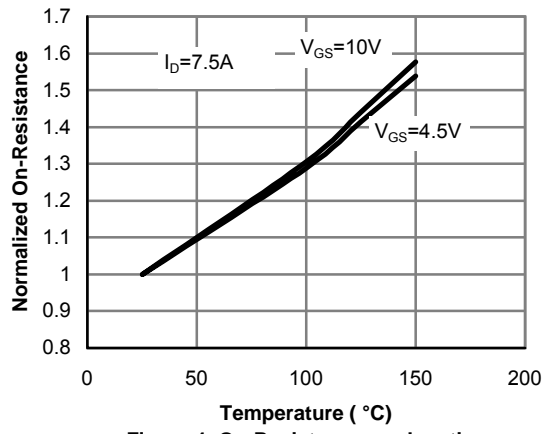


Figure 4: On-Resistance vs. Junction Temperature

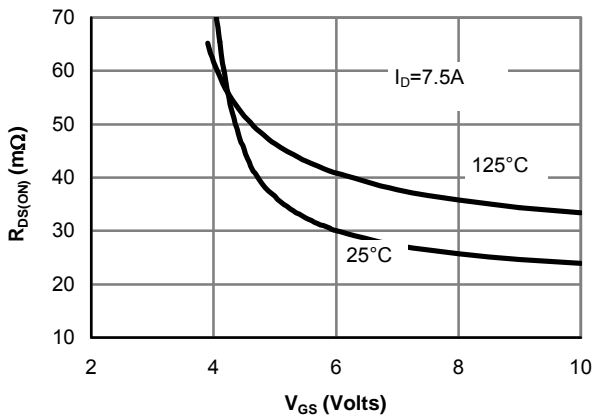


Figure 5: On-Resistance vs. Gate-Source Voltage

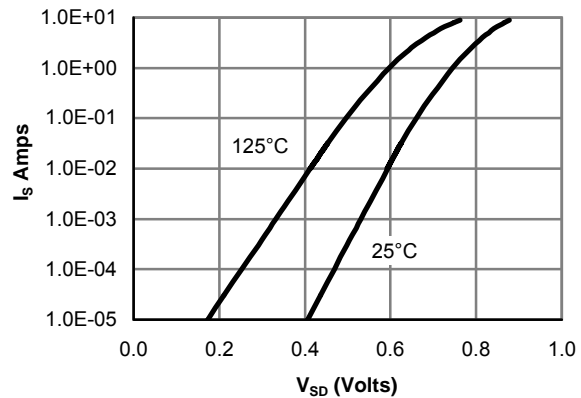


Figure 6: Body diode characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: N-CANNEL

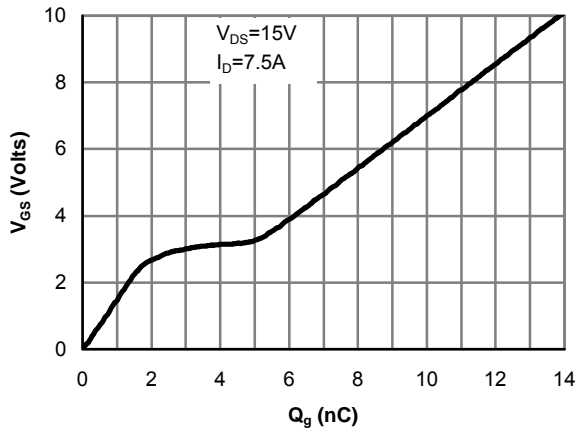


Figure 7: Gate-Charge characteristics

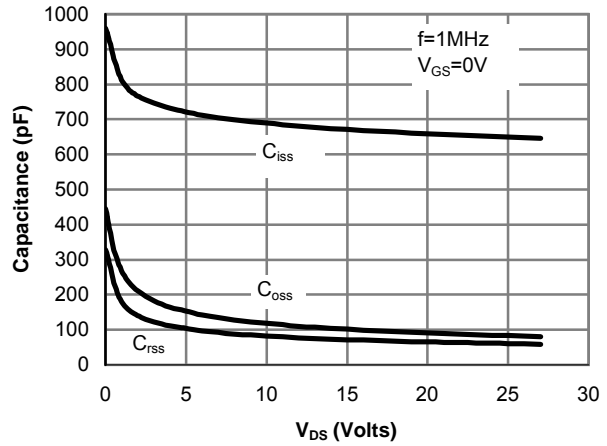


Figure 8: Capacitance Characteristics

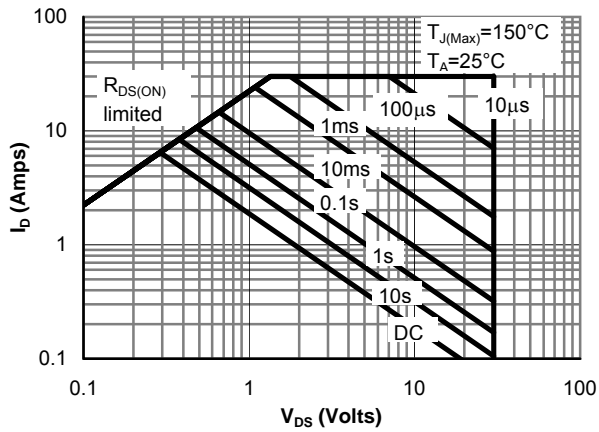


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

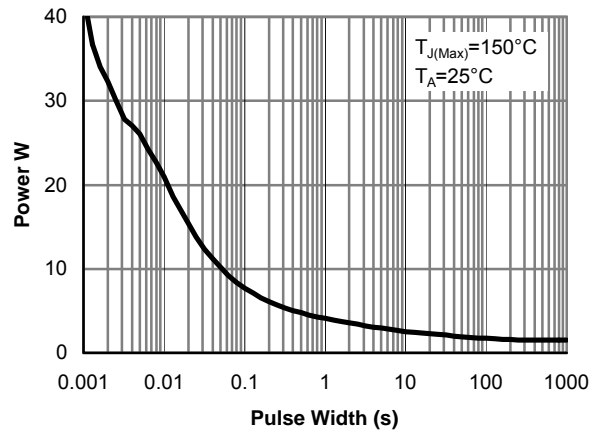


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

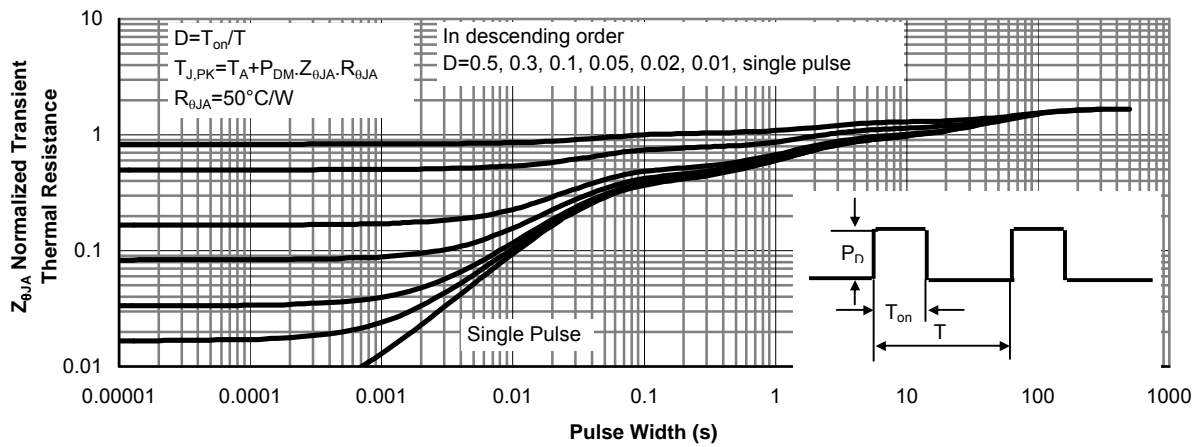


Figure 11: Normalized Maximum Transient Thermal Impedance

p-channel MOSFET Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-1.2	-2	-2.4	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}, V_{DS}=-5\text{V}$	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}, I_D=-6.6\text{A}$ $T_J=125^\circ\text{C}$		28 37	35 45	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}, I_D=-5\text{A}$		44	58	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}, I_D=-6.6\text{A}$		13		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}, V_{GS}=0\text{V}$		-0.76	-1	V
I_S	Maximum Body-Diode Continuous Current				-4.2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-15\text{V}, f=1\text{MHz}$		920	1100	pF
C_{oss}	Output Capacitance		190		pF	
C_{rss}	Reverse Transfer Capacitance		122		pF	
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		3.6	4.4	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge (10V)	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, I_D=-6.6\text{A}$		18.5	22.2	nC
$Q_g(4.5\text{V})$	Total Gate Charge (4.5V)		9.6	11.6	nC	
Q_{gs}	Gate Source Charge		2.7		nC	
Q_{gd}	Gate Drain Charge		4.5		nC	
$t_{D(on)}$	Turn-On Delay Time		7.7		ns	
t_r	Turn-On Rise Time	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, R_L=2.3\Omega,$ $R_{GEN}=3\Omega$		5.7		ns
$t_{D(off)}$	Turn-Off Delay Time		20.2		ns	
t_f	Turn-Off Fall Time		9.5		ns	
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-6.6\text{A}, dI/dt=100\text{A}/\mu\text{s}$		20	24	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-6.6\text{A}, dI/dt=100\text{A}/\mu\text{s}$		8.8		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

Rev 3 : June 2005

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: P-CHANNEL

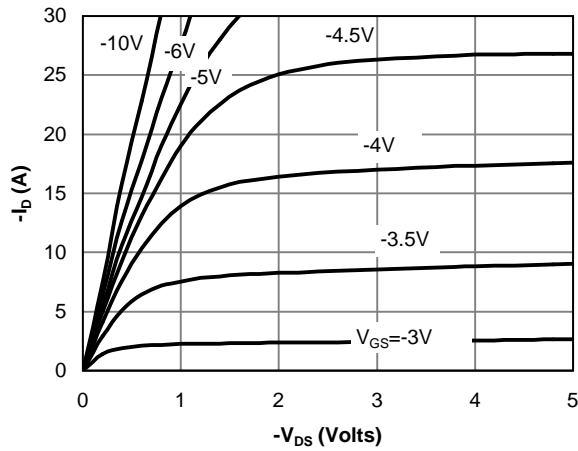


Fig 1: On-Region Characteristics

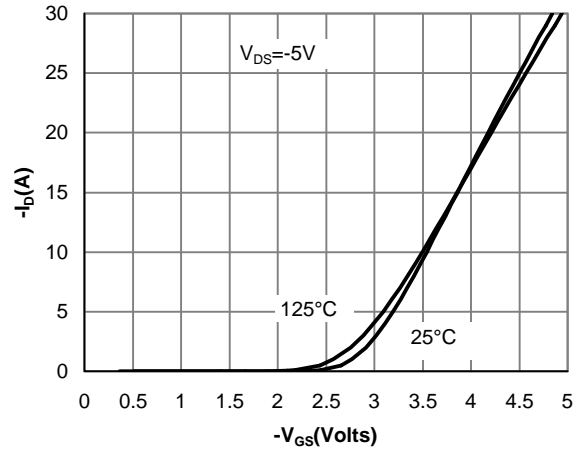


Figure 2: Transfer Characteristics

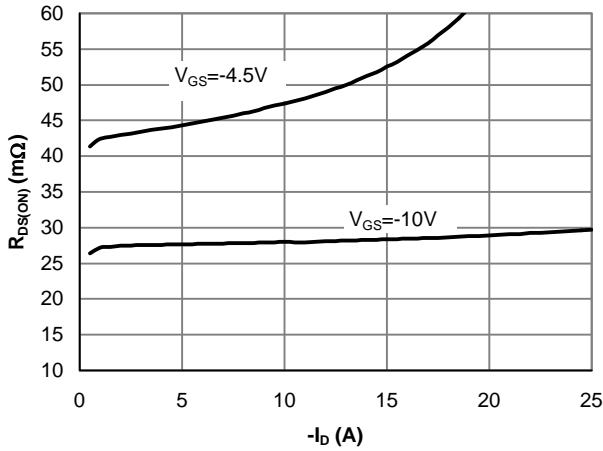


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

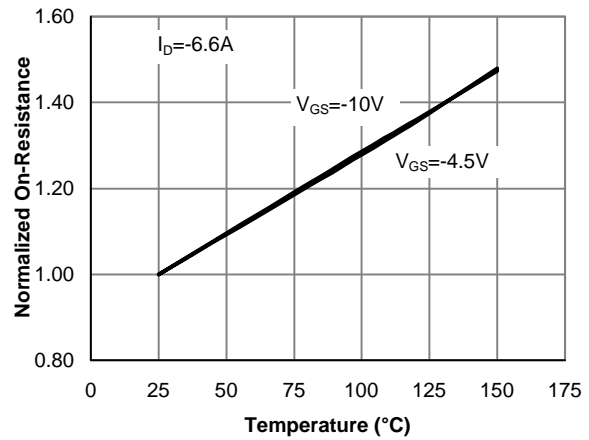


Figure 4: On-Resistance vs. Junction Temperature

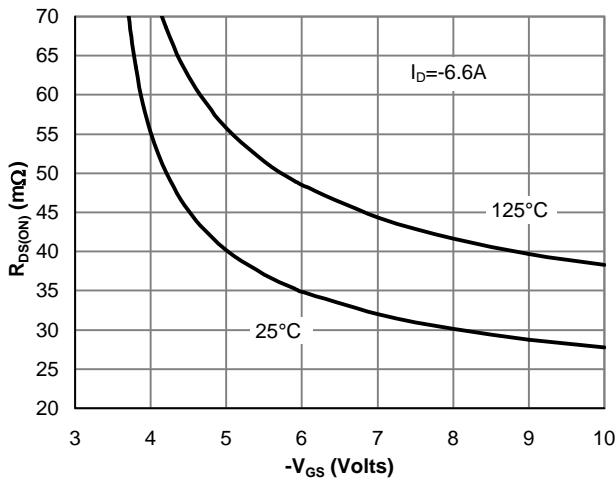


Figure 5: On-Resistance vs. Gate-Source Voltage

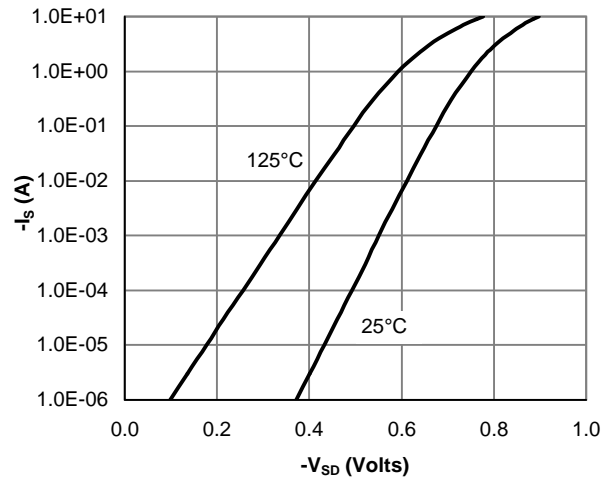


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: P-CHANNEL

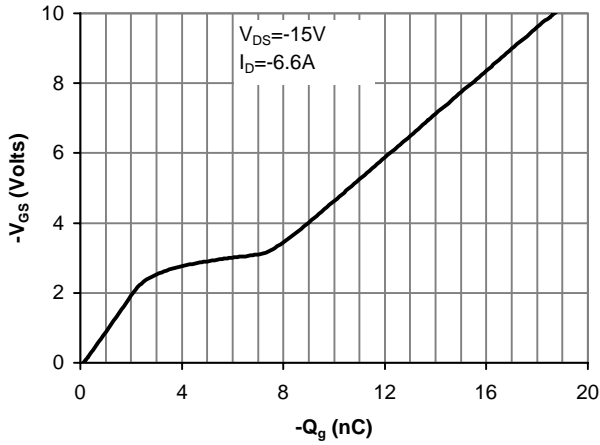


Figure 7: Gate-Charge Characteristics

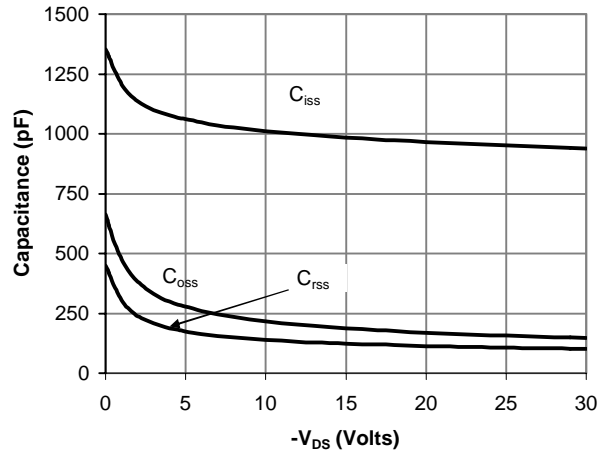


Figure 8: Capacitance Characteristics

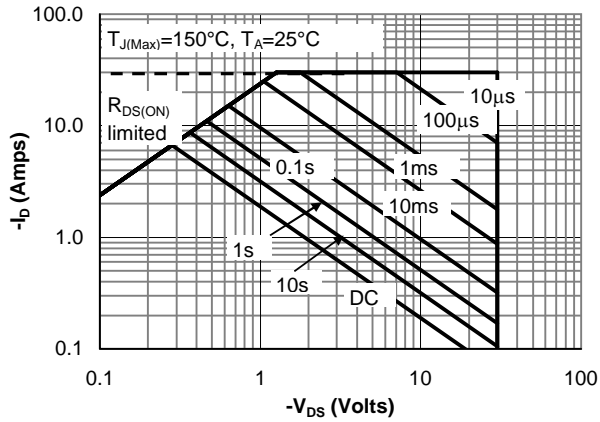


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

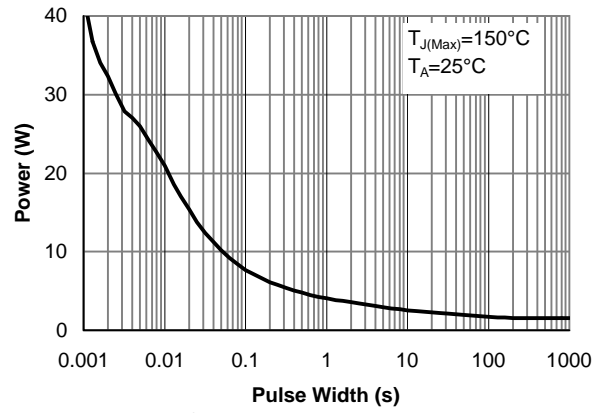


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

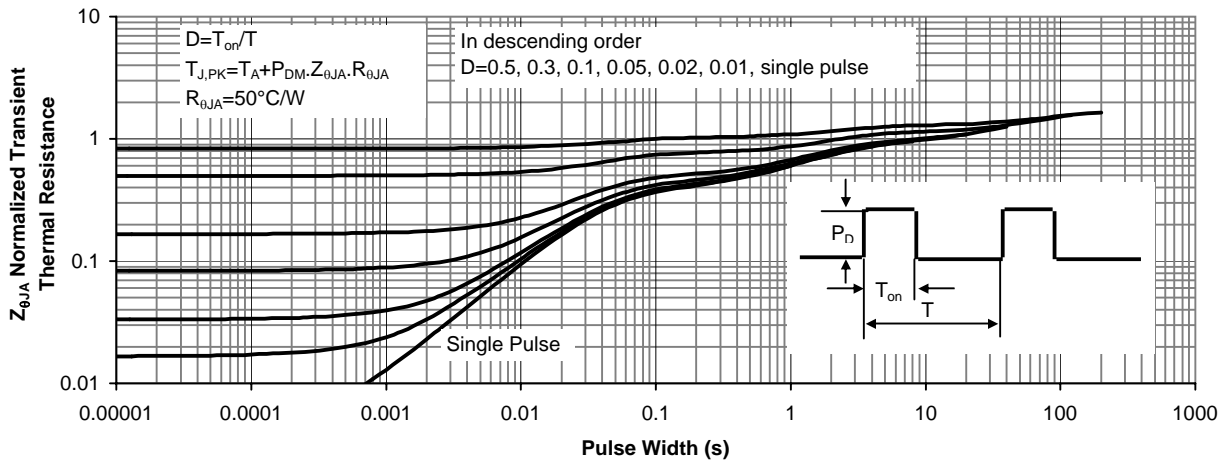


Figure 11: Normalized Maximum Transient Thermal Impedance